

Isc P-Channel MOSFET Transistor

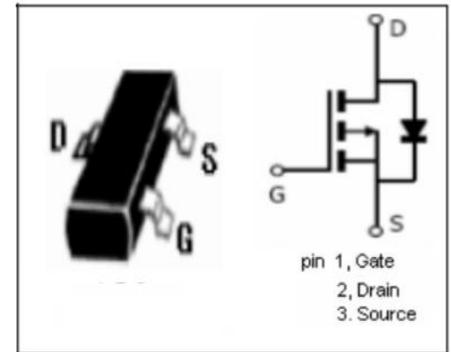
IRLML6302

• FEATURES

- With SOT-23 package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

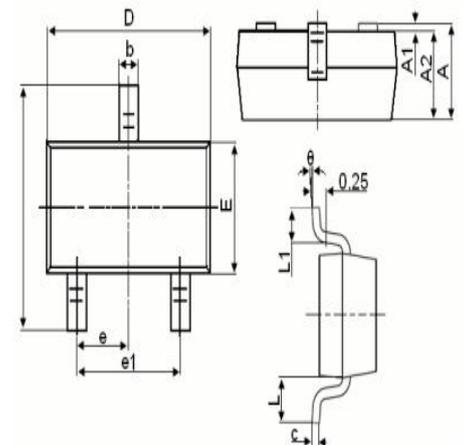
• APPLICATIONS

- Switching applications



• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--------------------------------------------------------------------------|----------------|------|
| V _{DSS} | Drain-Source Voltage | -20 | V |
| V _{GSS} | Gate-Source Voltage | ± 12 | V |
| I _D | Drain Current-Continuous T _c =25°C T _c =70°C | -0.78 -0.26 | A |
| I _{DM} | Drain Current-Single Pulsed | -4.9 | A |
| P _D | Total Dissipation @T _c =25°C | 540 | mW |
| T _{ch} | Max. Operating Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55~150 | °C |



| Symbol | Dimensions in Millimeters | |
|--------|---------------------------|-------|
| | MIN. | MAX. |
| A | 0.900 | 1.150 |
| A1 | 0.000 | 0.100 |
| A2 | 0.900 | 1.050 |
| b | 0.300 | 0.500 |
| c | 0.080 | 0.150 |
| D | 2.800 | 3.000 |
| E | 1.200 | 1.400 |
| E1 | 2.250 | 2.550 |
| e | 0.950TYP | |
| e1 | 1.800 | 2.000 |
| L | 0.550REF | |
| L1 | 0.300 | 0.500 |
| θ | 0° | 8° |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|-----------------------|---------------------------------------|-----|------|
| R _{th(ch-a)} | Channel-to-ambient thermal resistance | 230 | °C/W |

Isc P-Channel MOSFET Transistor**IRLML6302****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------|--------------------------------|---------------------------------------------------------------------------------------------------------|------|-----|-----------|-----------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V; I_D=-0.25mA$ | -20 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}; I_D=-0.25mA$ | -0.7 | | -1.5 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}= -4.5V; I_D=-0.61A$ | | | 600 | $m\Omega$ |
| I_{GSS} | Gate-Source Leakage Current | $V_{GS}= \pm 12V; V_{DS}=0V$ | | | ± 0.1 | μA |
| I_{DSS} | Drain-Source Leakage Current | $V_{DS}=-16V; V_{GS}= 0V; T_j=25^{\circ}\text{C}$ $V_{DS}=-16V; V_{GS}= 0V; T_j=150^{\circ}\text{C}$ | | | -1 -25 | μA |
| V_{SDF} | Diode forward voltage | $I_{SD}=-0.61A, V_{GS}= 0V$ | | | -1.2 | V |

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